

### IAP100T120 Integrated Advanced PowerStack

100A / 1200V Three-Phase-Bridge IGBT Inverter



#### FEATURES INCLUDE

- Compact Size 8.00" H X 17.56" W X 11.00" D
- DC Bus Voltages to 850VDC
- Snubber-less operation to 650VDC
- Switching frequencies to over 20kHz
- Protective circuitry with fail-safe opto-isolated fault annunciation, including:
  - OverCurrent
    - Short circuit P.S. UnderVoltage
    - OverVoltage
  - OverTemperature
- Opto-isolated or fiber-optic gate drive and fault signal output for electrical isolation and noise immunity
- Integrated cooling with temperature sensors and feedback
- Many options Diode/SCR Front End, etc.

#### **Configurable Power**

The IAP100T120 PowerStack is a flexible, highly integrated IGBT based power assembly with a wide range of applications. These include inverters for motor controls, switch mode power supplies (SMPS), UPS, welders, renewable energy, energy storage, etc. The IAP100T120 PowerStack can be operated at frequencies to over 20kHz. The IAP100T120 PowerStack can be configured as a full bridge or three-phase bridge inverter mounted on an air-cooled or liquid-cooled heat sink. Configurations include options for (full, half or no control) converter input circuitry, inverter output circuitry, cooling and a wide variety of drivers and safety features for the converter front end and IGBT inverter output stage.

To operate at high switching frequencies, the IAP100T120 PowerStack utilizes a low inductance laminated bus structure, optically isolated or fiber optically coupled gate drive interfaces, isolated gate power supplies and a DC-link

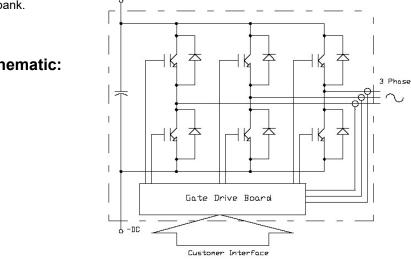
capacitor bank.

Schematic:

The IAP100T120 PowerStack provides built in protection features including: over voltage, under voltage lockout, over current, over temperature, short circuit and optional airflow or liquid flow indicators.

Flexibility is a key feature of the IAP100T120 PowerStack. Options include: a choice of converter front ends, rectifier, half or full SCR control, with or without SCR gate firing boards and soft-start circuitry. A choice of cooling methods, forced air or liquid is also available. Customer provided PWM is optically coupled or a fiber optic link can be provided to the IGBT interface. Current feedback is provided by Hall effect transducers.

The IAP100T120 PowerStack is rated to maximum input voltages up to 800 VDC, switching frequencies to over 20kHz, includes many safety features to protect the IGBTs and output circuitry and can be configured to meet vour application.



<sup>124</sup> Charlotte Avenue • Hicksville, NY 11801 • Ph: 516.935.2230 • Fax: 516.935.2603 • Website: www.appliedps.com Page 1 of 6 IAP100T120 Rev.A



### IAP100T120 PowerStack

Absolute Maximum Ratings – TJ=25°C unless otherwise specified						
General	Symbol	Value	Units			
IGBT Junction Temperature	TJ	-40 to +150	°C			
Storage Temperature	Tstg	-40 to +125	°C			
Voltage applied to DC terminals	Vcc	800	Volts			
Isolation voltage, AC 1 minute, 60Hz sinusoidal	Viso	2500	Volts			
IGBT Inverter						
Collector Current (T <sub>C</sub> =100°C)	lc	100	Amperes			
Peak Collector Current (TJ<150°C)	I <sub>СМ</sub>	200	Amperes			
Emitter Current	IE	100	Amperes			
Peak Emitter Current	IEM	200	Amperes			
Maximum Collector Dissipation (TJ<175°C)	Pcd	555	Watts			
Gate Drive Board						
Unregulated +24V Power Supply		30	Volts			
Regulated +15V Power Supply		18	Volts			
PWM Signal Input Voltage (Factory Settable from 3.3-15)		15	Volts			
Fault Output Supply Voltage		30	Volts			
Fault Output Current		50	mA			

#### IGBT Inverter Electrical Characteristics, TJ=25°C unless otherwise specified

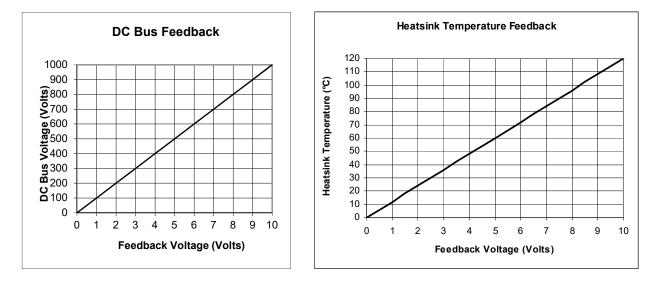
Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Collector Cutoff Current	ICES	V <sub>CE</sub> =V <sub>CES</sub> , V <sub>GE</sub> =0V	-	-	1	mA
Collector Emitter Seturation Voltage		I <sub>C</sub> =100A, T <sub>J</sub> =25°C	-	1.75	2.15	Volts
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	Ic=100A, TJ=125°C	-	2.05	-	Volts
Emitter-Collector Voltage	VEC	IE=100A	-	-	3.2	Volts
	t <sub>d(on)</sub>		-	-	130	ηs
Inductive Load Switching Times	tr	Vcc=600V	-	-	20	ηs
	t <sub>d(off)</sub>	I <sub>C</sub> =100A	-	-	300	ηs
	tr	V <sub>GE</sub> =15V	-	-	45	ηs
Diode Reverse Recovery Time	Trr	R <sub>G</sub> =1.6Ω	-	-	150	ηs
Diode Reverse Recovery Charge	Qrr		-	15.7	-	μC
DC Link Capacitance			-	3300	-	μF

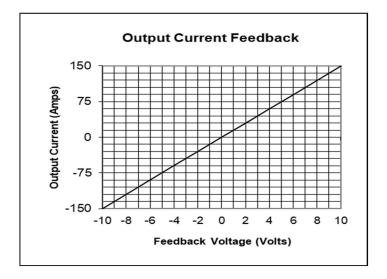
#### **Thermal and Mechanical Parameters**

Parameter	Symbol	<b>Test Conditions</b>	Min	Тур	Max	Units
IGBT Thermal Resistance, Junction to Case	RΘ(j-c)	Per IGBT ½	-	*	0.27	°C/W
		module				
FWD Thermal Resistance, Junction to Case	R⊝(j-c)	Per FWD 1/2 module	-	-	0.48	°C/W
Heatsink Thermal Resistance	R⊝(s-a)	1500 LFM airflow	-	.045	-	°C/W
Mounting Torque, AC terminals			-	75	90	In-lb
Mounting Torque, DC terminals			-	130	150	In-lb
Mounting Torque, case mounting			-	130	150	In-lb
Weight			-	21	-	lb



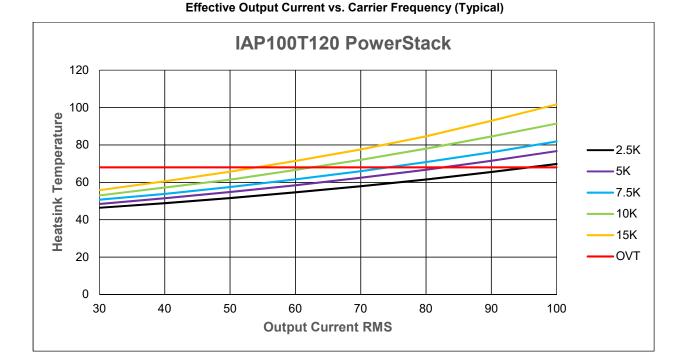
Gate Drive Board Electrical Characteristics				
Parameter	Min	Тур	Max	Units
Unregulated +24V Power Supply	20	24	30	Volts
Regulated +15V Power Supply	14.4	15	18	Volts
PWM Input On Threshold (Factory Settable from 3.3 to 15)	12	15	-	Volts
PWM Inout Off Threshold	-	0	2	Volts
Output Overcurrent Trip	-	150	-	Amperes
Overtemperature Trip	78	80	82	°C
Overvoltage Trip	-	900	-	Volts
DC Link Voltage Feedback	See F	igure B	elow	Volts
Heatsink Temperature Feedback See Figure Below		Volts		
Output Current Feedback	See F	See Figure Below Volt		







#### Performance Curves



Conditions	Symbol	Value	Units	
Ambient Temperature	TA	40	°C	
DC Bus Voltage	Vcc	600	Volts	
Load Power Factor	COS Φ	0.8		
IGBT Saturation Voltage	V <sub>CE(sat)</sub>	Typical @ Tյ=125°C	Volts	
IGBT Switching Loss	Esw	Typical @ Tյ=125°C	mJ	
Airflow	-	1500	LFM	
Switching Conditions	Thre	Three-phase PWM, 60Hz sinusoidal output		

#### Options for the BAP300T120-XX

		Option Number							
Option	01	02	03	04	05	06	07	08	09
Blower	X		X		X		X		X
Half-Control SCR Converter		X	X						
Full Control SCR Converter				X	X				
Diode Converter						X	X		
Dual Inverter								Х	Х



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Interface

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Pin #	Signal Name	Description	
1	Shield	Connected to circuit ground	
2	PWM A-	0-15V signal controlling the duty cycle of A- IGBT	
3	Phase A Error <sup>1</sup>	Open collector output, external pull-up resistor required.	
		LOW=No Error; Floating=Phase A overcurrent or short circuit	
4	PWM A+	0-15V signal controlling the duty cycle of A+ IGBT	
5	PWM B-	0-15V signal controlling the duty cycle of B- IGBT	
6	Phase B Error <sup>1</sup>	Open collector output, external pull-up resistor required.	
		LOW=No Error; Floating=Phase B overcurrent or short circuit	
7	PWM B+	0-15V signal controlling the duty cycle of B+ IGBT	
8	PWM C-	0-15V signal controlling the duty cycle of C- IGBT	
9	Phase C Error <sup>1</sup>	Open collector output, external pull-up resistor required.	
		LOW=No Error; Floating=Phase C overcurrent or short circuit	
10	PWM C+	0-15V signal controlling the duty cycle of C+ IGBT	
11	OverTemp <sup>1</sup>	Open collector output, external pull-up resistor required.	
		LOW=No Error; Floating=Heatsink overtemp	
12	Not Connected	0-15V signal controlling the duty cycle of C+ IGBT	
13	DC Link Voltage	Analog voltage representation of DC link voltage	
14	24VDC Input Power <sup>2</sup>	20-30VDC input voltage range	
15	24VDC Input Power <sup>2</sup>	20-30VDC input voltage range	
16	15VDC Input Power <sup>2</sup>	14.4-18VDC input voltage range	
17	15VDC Input Power <sup>2</sup>	14.4-18VDC input voltage range	
18	GND	Ground reference for 15 and 24VDC inputs	
19	GND	Ground reference for 15 and 24VDC inputs	
20	Heatsink Temperature	Analog voltage representation of heatsink temperature	
21	GND <sup>3</sup>	Tied to pins 18 and 19	
22	I <sub>OUT</sub> Phase A	Analog voltage representation of phase A output current	
23	GND <sup>3</sup>	Tied to pins 18 and 19	
24	IOUT Phase B	Analog voltage representation of phase B output current	
25	GND <sup>3</sup>	Tied to pins 18 and 19	
26	Iout Phase C	Analog voltage representation of phase C output current	

#### NOTES:

1.	Open collectors can be pulled up to 30VDC Max and sink 50mA continuous.
2.	<b><u>DO NOT</u></b> connect a 15VDC and 24VDC source to the unit at the same time. Use one or
	the other.
3.	GND signals to be used for analog feedback signals, i.e. twisted pair with I <sub>OUT</sub> Phase A.

#### **Gate Drive Interface Connector**

Description	Symbol	Туре	Manufacturer				
Gate Drive Interface Header	J1	0.100" x 0.100" latching header, 26 pin	3M #3429-6002 or equivalent				
Recommending Mating Socket	-	0.100" x 0.100" IDC socket, 26 pin	3M #3399-7600 or equivalent				
Recommended Strain Relief	-	Plastic strain relief	3M #3448-3026 or equivalent				



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#### **Mechanical Information**

